

N-channel LFPAK 60 V 15.7 mΩ standard level MOSFET

Rev. 02 — 1 April 2010

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

### 1.4 Quick reference data

### Table 1. Quick reference

- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

Table 1.	Quick reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	60	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	-	-	44	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	74	W
Tj	junction temperature		-55	-	175	°C
Avalance	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy		-	-	45	mJ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 30 \text{ A};$	-	4.4	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 30 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{and } \frac{15}{2}}$	-	20	-	nC

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Table 1.	Quick reference	.continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cl	naracteristics					
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	25	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	12.3	15.7	mΩ

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	
3	S	source		
4	G	gate	Q	
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK)	

### 3. Ordering information

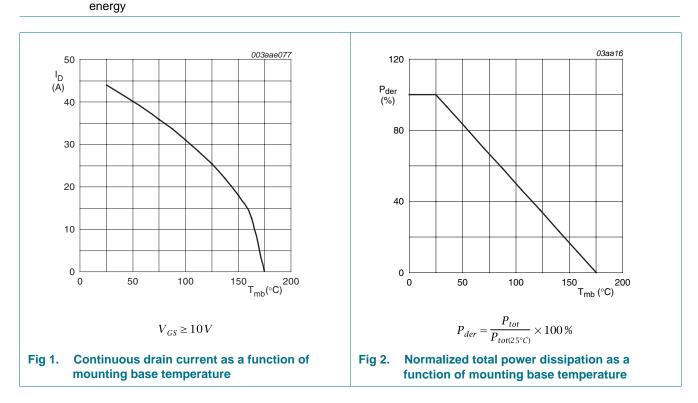
Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PSMN017-60Y	S LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669	

### 4. Limiting values

#### Table 4. Limiting values

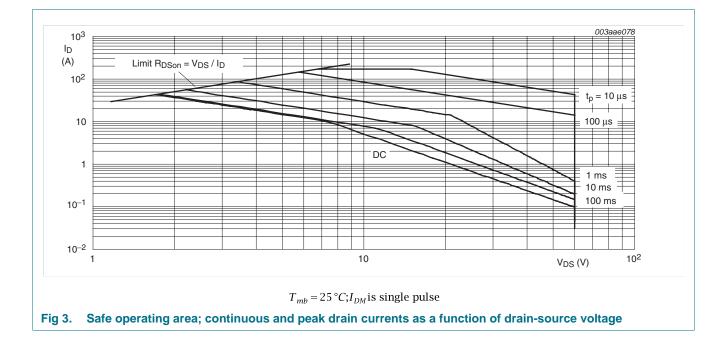
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	60	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	31	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	44	А
I <sub>DM</sub>	peak drain current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	174	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	74	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-dr	ain diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	44	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	174	А
Avalanche	e ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche epergy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 45 A; $V_{sup}$ $\leq$ 60 V; $R_{GS}$ = 50 $\Omega;$ unclamped	-	45	mJ



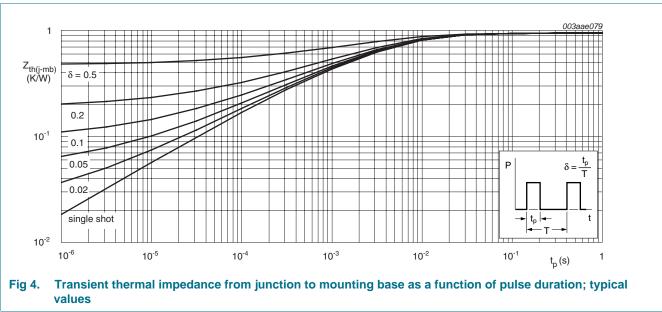
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#### **Thermal characteristics** 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.9	2.03	K/W



### 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics	Conditions		чур	ιτίαλ	Unit
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = -55 °C	54	-	_	V
V (BR)DSS	breakdown voltage	$I_D = 250 \ \mu\text{A}, \ V_{GS} = 0 \ V, \ I_J = 55 \ C$ $I_D = 250 \ \mu\text{A}, \ V_{GS} = 0 \ V; \ T_i = 25 \ C$	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 200 \mu$ s, $V_{GS} = 0.05, I_j = 25 ^{\circ}\text{C}$ ; see Figure 10	2	3	4	V
- 00(11)	voltage	and $\frac{11}{12}$	_	-		-
V <sub>GSth</sub>		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; \text{see } Figure 11$	-	-	4.7	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 11</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	2	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	24.7	36.1	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 100 °C; see <u>Figure 12</u>	-	-	25	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	12.3	15.7	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1	1.5	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub> total ga	total gate charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 and 15	-	20	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	16.5	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	6.4	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	3.5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	2.9	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 and 15	-	4.4	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$V_{DS} = 30$ V; see <u>Figure 14</u> and <u>15</u>	-	4.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C;	-	1172	-	pF
C <sub>oss</sub>	output capacitance	see Figure 16	-	164	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	96	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_L$ = 1 $\Omega$ ; $V_{GS}$ = 10 V;	-	13	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	6.4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	27	-	ns
t <sub>f</sub>	fall time		-	12.7	-	ns

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Symbol

Source-drain diode

### **PSMN017-60YS**

Max

Unit

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Min

Тур

$V_{SD}$	source-drain voltage	$I_S$ = 15 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see Figure 17	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		33.4	-	ns
Qr	recovered charge	$V_{DS} = 30 V$	-	38.9	-	nC
40 9 <sub>fs</sub> (S)		003aae082 50 I <sub>D</sub> (A)			003aae081	
30		30				
20		20				
			= 175 °C	Т	i = 25 ∘C	
0	0 10 20	30 I <sub>D</sub> (A) 40 0	2	4	6 V <sub>GS</sub> (V)	i
-	$T_j = 25 ^{\circ}C; V_{DS} =$ Forward transconductan drain current; typical value	ce as a function of Fig 6. Transfer cha		stics: drain		
2000		003aae083 50 R <sub>DSon</sub>			003aae085	
C (pF) 1500		$C_{iss}$ (m $\Omega$ ) 40				
1000		C <sub>rss</sub> 30				
		20				
500		10				
C	0 2 4	6 V <sub>GS</sub> (V) 8 0 0 5	1	0 15	V <sub>GS</sub> (V) <sup>20</sup>	)
	$V_{DS} = 0V; f = 11$	MHz	$T_j = 25 ^{\circ}C$	$I_{i} = 10A$		
	Input and reverse transfe function of gate-source v	er capacitances as a Fig 8. Drain-sourc	-		ce as a f	unction

#### Table 6. Characteristics ...continued

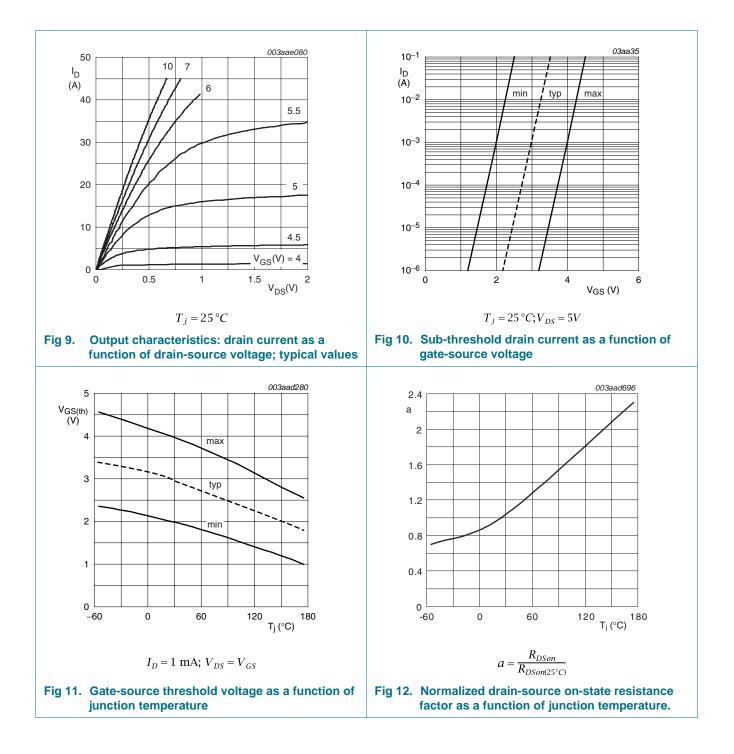
Parameter

Conditions

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### **PSMN017-60YS**

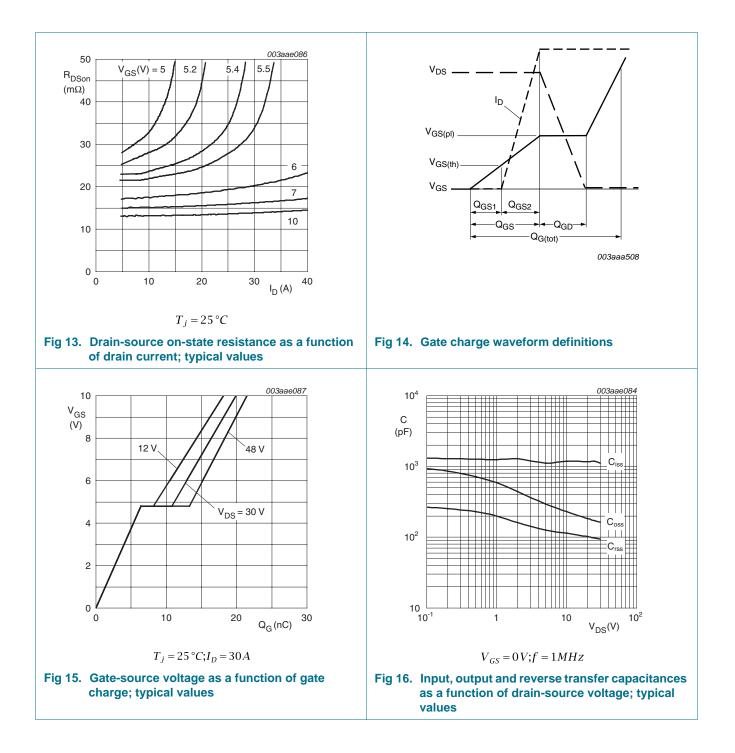
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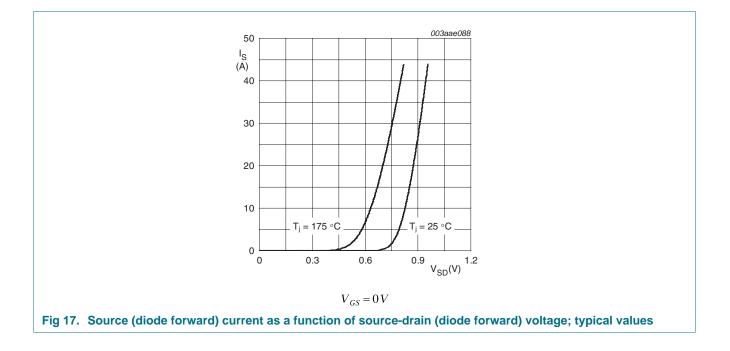
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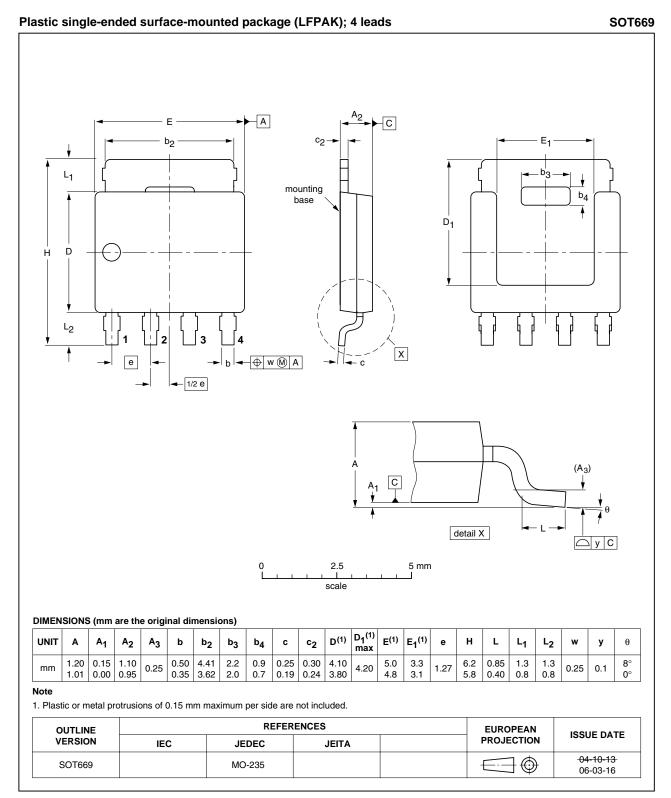
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### 7. Package outline



#### Fig 18. Package outline SOT669 (LFPAK)

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### 8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN017-60YS_2	20100401	Product data sheet	-	PSMN017-60YS_1
Modifications:	<ul> <li>Status cha</li> </ul>	nged from objective to pr	oduct.	
	<ul> <li>Various ch</li> </ul>	anges to content.		
PSMN017-60YS_1	20100122	Objective data sheet	-	-

### 9. Legal information

### 9.1 Data sheet status

Document status [1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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